

## NTD23N03RT4 Datasheet



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DiGi Electronics Part Number NTD23N03RT4-DG

Manufacturer onsemi

Manufacturer Product Number NTD23N03RT4

Description MOSFET N-CH 25V 3.8A/17.1A DPAK

Detailed Description N-Channel 25 V 3.8A (Ta), 17.1A (Tc) 1.14W (Ta), 22

.3W (Tc) Surface Mount DPAK



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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
NTD23N03RT4	onsemi
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
25 V	3.8A (Ta), 17.1A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4V, 5V	45m0hm @ 6A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250μA	3.76 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	225 pF @ 20 V
FET Feature:	Power Dissipation (Max):
	1.14W (Ta), 22.3W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
DPAK	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
NTD22	

## **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
RoHS non-compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

## **Power MOSFET**

## 23 A, 25 V, N-Channel DPAK

#### **Features**

- Planar HD3e Process for Fast Switching Performance
- Low R<sub>DS(on)</sub> to Minimize Conduction Loss
- Low Ciss to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- Pb-Free Packages are Available

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	25	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	±20	Vdc
Thermal Resistance, Junction-to-Case Total Power Dissipation @ T <sub>C</sub> = 25°C Drain Current	R <sub>θJC</sub> P <sub>D</sub>	5.6 22.3	°C/W W
<ul> <li>Continuous @ T<sub>C</sub> = 25°C, Chip</li> <li>Continuous @ T<sub>C</sub> = 25°C,</li> <li>Limited by Package</li> </ul>	I <sub>D</sub> I <sub>D</sub>	23 17.1	A A
- Single Pulse	I <sub>DM</sub>	40	Α
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	76	°C/W
Total Power Dissipation @ T <sub>A</sub> = 25°C Drain Current – Continuous @ T <sub>A</sub> = 25°C	P <sub>D</sub> I <sub>D</sub>	1.64 4.5	W A
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	110	°C/W
Total Power Dissipation @ T <sub>A</sub> = 25°C Drain Current – Continuous @ T <sub>A</sub> = 25°C	P <sub>D</sub> I <sub>D</sub>	1.14 3.8	W A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to 150	°C
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. When surface mounted to an FR4 board using 0.5 sq in pad size.
- When surface mounted to an FR4 board using minimum recommended pad size.

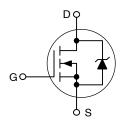


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V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
25 V	32 m $\Omega$	23 A

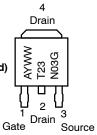
#### **N-CHANNEL**



#### MARKING DIAGRAMS

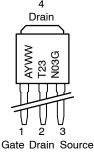


DPAK
CASE 369AA
(Surface Mounted)
STYLE 2





DPAK-3 CASE 369D (Straight Lead) STYLE 2



T23N03 = Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

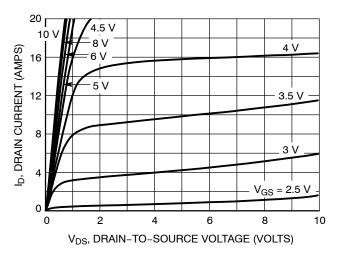
### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Cha	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			•			
Drain-to-Source Breakdown Voltag (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μA Temperature Coefficient (Positive)	V(br) <sub>DSS</sub>	25 -	28 -	- -	Vdc mV/°C	
Zero Gate Voltage Drain Current $(V_{DS} = 20 \text{ Vdc}, V_{GS} = 0 \text{ V})$ $(V_{DS} = 20 \text{ Vdc}, V_{GS} = 0 \text{ V})$	(dc) (dc, T <sub>J</sub> = 150°C)	I <sub>DSS</sub>	- -	_ _	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = ±20 Vdc, V <sub>DS</sub> = 0	Vdc)	I <sub>GSS</sub>	-	-	±100	nAdc
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage (Note 3) $(V_{DS} = V_{GS}, I_D = 250 \mu Ad$ Threshold Temperature Coefficient (	c) Negative)	V <sub>GS(th)</sub>	1.0	1.8	2.0 -	Vdc mV/°C
Static Drain-to-Source On-Resista $(V_{GS} = 4.5 \text{ Vdc}, I_D = 6 \text{ Add})$ $(V_{GS} = 10 \text{ Vdc}, I_D = 6 \text{ Add})$	R <sub>DS(on)</sub>	- -	50.3 32.3	60 45	mΩ	
Forward Transconductance (Note 3) (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 6 Add	9FS	_	13	_	Mhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance		C <sub>iss</sub>	-	225	_	pF
Output Capacitance	$(V_{DS} = 20 \text{ Vdc}, V_{GS} = 0 \text{ V, f} = 1 \text{ MHz})$	C <sub>oss</sub>	-	108	_	
Transfer Capacitance		C <sub>rss</sub>	-	48	_	
SWITCHING CHARACTERISTICS	(Note 4)					
Turn-On Delay Time		t <sub>d(on)</sub>	-	2.0	-	ns
Rise Time	(V <sub>GS</sub> = 10 Vdc, V <sub>DD</sub> = 10 Vdc,	t <sub>r</sub>	-	14.9	_	
Turn-Off Delay Time	$I_D = 6 \text{ Adc}, R_G = 3 \Omega)$	t <sub>d(off)</sub>	-	9.9	_	
Fall Time		t <sub>f</sub>	-	2.0	-	1
Gate Charge		$Q_T$	-	3.76	-	nC
	$(V_{GS} = 4.5 \text{ Vdc}, I_D = 6 \text{ Adc}, V_{DS} = 10 \text{ Vdc})$ (Note 3)	Q <sub>1</sub>	-	1.7	-	1
	V <sub>DS</sub> = 10 VdS) (Note 5)		-	1.6	-	
SOURCE-DRAIN DIODE CHARAC	TERISTICS					
Forward On-Voltage	$(I_S = 6 \text{ Adc}, V_{GS} = 0 \text{ Vdc}) \text{ (Note 3)}$ $(I_S = 6 \text{ Adc}, V_{GS} = 0 \text{ Vdc}, T_J = 125^{\circ}\text{C})$	V <sub>SD</sub>	_ _	0.87 0.74	1. <u>2</u> –	Vdc
Reverse Recovery Time		t <sub>rr</sub>	-	8.7	-	ns
	(I <sub>S</sub> = 6 Adc, V <sub>GS</sub> = 0 Vdc,	ta	-	5.2	-	
	dl <sub>S</sub> /dt = 100 A/μs) (Note 3)	t <sub>b</sub>	-	3.5	-	
Reverse Recovery Stored Charge		Q <sub>RR</sub>	-	0.003	_	μC

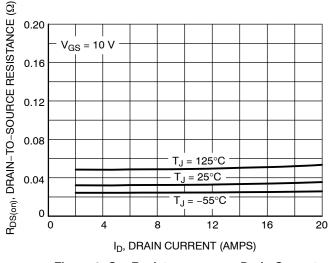
Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.



20 V<sub>DS</sub> ≥ 10 V NIVBU 12 12 13 14 T<sub>J</sub> = 25°C T<sub>J</sub> = -55°C 0 0 1 2 3 4 V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (VOLTS)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



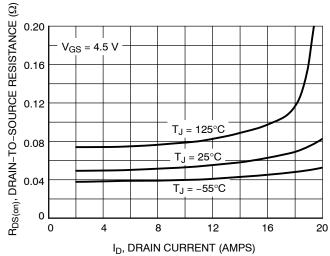
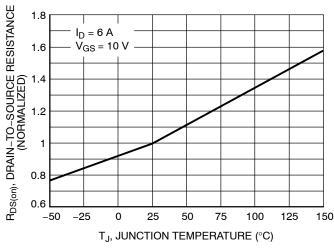


Figure 3. On-Resistance versus Drain Current and Temperature

Figure 4. On-Resistance versus Drain Current and Temperature



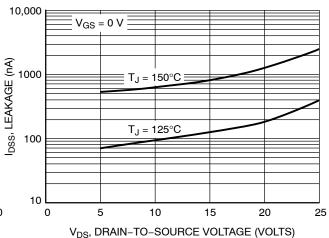


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current versus Voltage

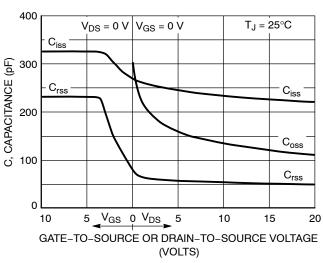


Figure 7. Capacitance Variation

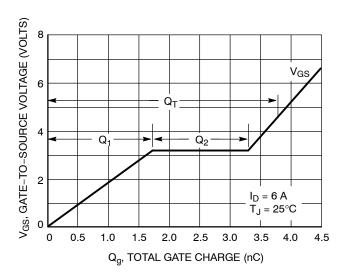


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

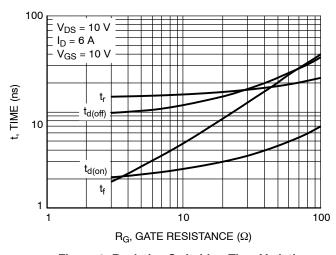


Figure 9. Resistive Switching Time Variation versus Gate Resistance

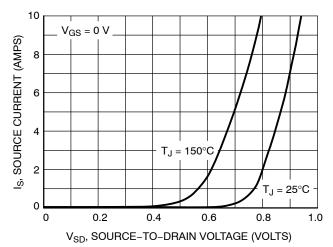


Figure 10. Diode Forward Voltage versus Current

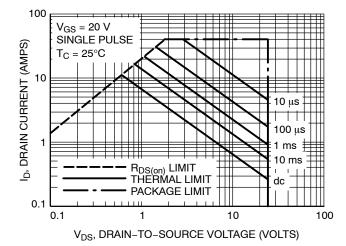


Figure 11. Maximum Rated Forward Biased Safe Operating Area

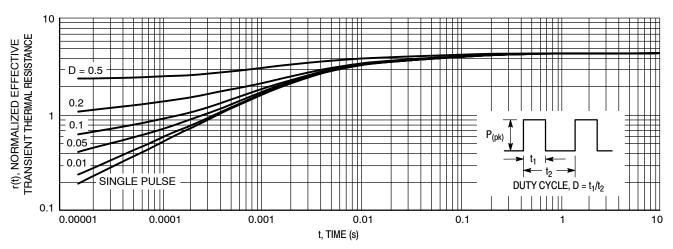


Figure 12. Thermal Response

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTD23N03RG	DPAK (Pb-Free)	75 Units/Rail
NTD23N03R-1G	DPAK-3 (Pb-Free)	75 Units/Rail
NTD23N03RT4	DPAK	2500 Tape & Reel
NTD23N03RT4G	DPAK (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



## **MECHANICAL CASE OUTLINE**

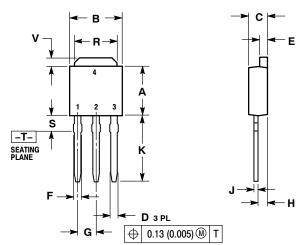
**PACKAGE DIMENSIONS** 

#### **DPAK INSERTION MOUNT**

CASE 369 ISSUE O

**DATE 02 JAN 2000** 





- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1 27

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		STYLE 5:		STYLE 6:	
PIN 1.	BASE	PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	GATE	PIN 1.	MT1
2.	COLLECTOR	2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE	2.	MT2
3.	EMITTER	3.	SOURCE	3.	ANODE	3.	GATE	3.	CATHODE	3.	GATE
4.	COLLECTOR	4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE	4.	MT2

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DESCRIPTION:	DPAK INSERTION MOUNT		PAGE 1 OF 1		

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#### **MECHANICAL CASE OUTLINE** PACKAGE DIMENSIONS

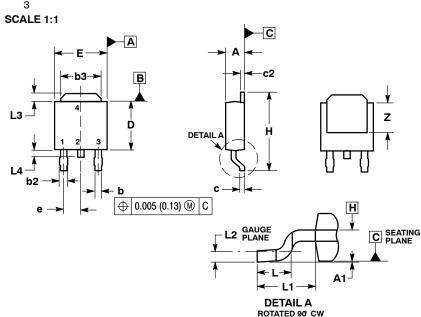
## **DPAK (SINGLE GUAGE)** CASE 369AA **ISSUE B**

**DATE 03 JUN 2010** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCHES.
  3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE
- DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
Е	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	



## STYLE 1: PIN 1. BASE

2. COLLECTOR 3. EMITTER 4. COLLECTOR

## STYLE 2: PIN 1. GATE

2. DRAIN 3. SOURCE 4. DRAIN

#### STYLE 3: PIN 1. ANODE

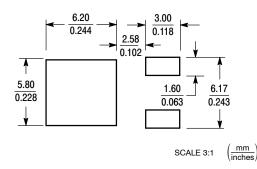
2. CATHODE 3. ANODE CATHODE

# STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE

#### STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE

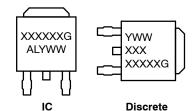
STYLE 6: PIN 1. MT1 2. MT2 3. GATE STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER COLLECTOR

## **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC** MARKING DIAGRAM\*



XXXXXX = Device Code Α = Assembly Location L = Wafer Lot ٧ = Year = Work Week WW = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1		

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